

To our customers,

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## Old Company Name in Catalogs and Other Documents

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On April 1<sup>st</sup>, 2010, NEC Electronics Corporation merged with Renesas Technology Corporation, and Renesas Electronics Corporation took over all the business of both companies. Therefore, although the old company name remains in this document, it is a valid Renesas Electronics document. We appreciate your understanding.

Renesas Electronics website: <http://www.renesas.com>

April 1<sup>st</sup>, 2010  
Renesas Electronics Corporation

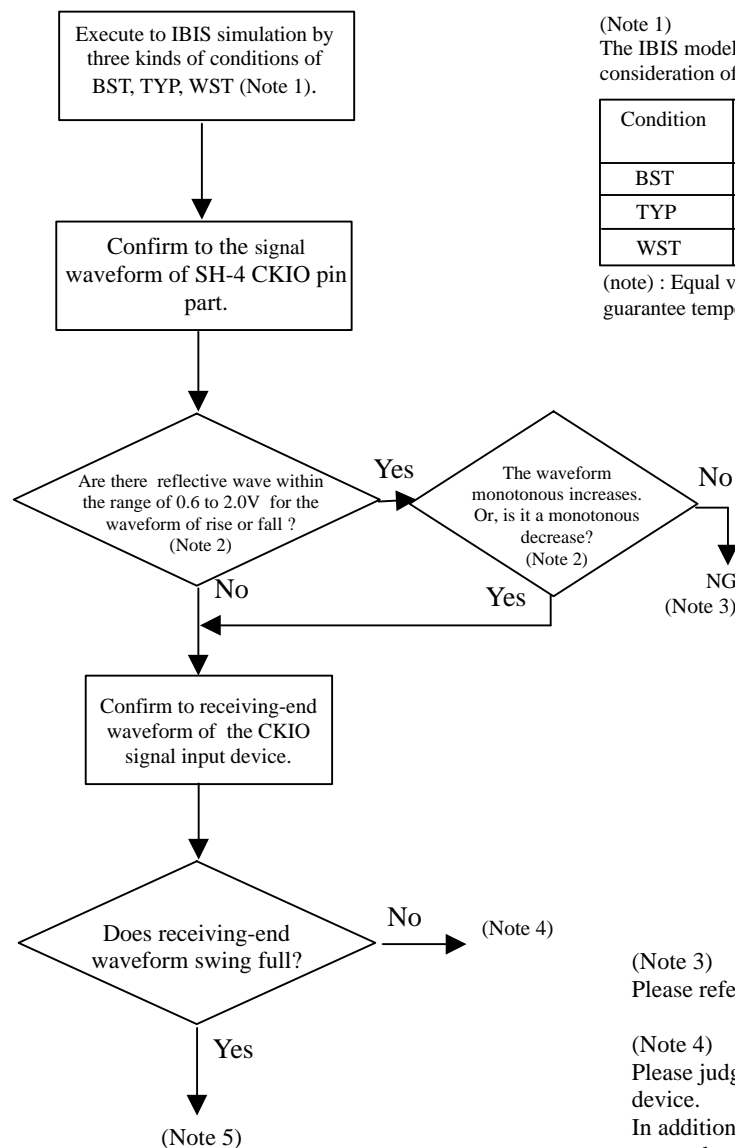
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## 2. Judgment method

Figure 1 shows the method of judgement of the IBIS simulation result.



(Note 1)

The IBIS model of SH-4 can be selected following three conditions, in consideration of power-supply voltage, temperature, and device disunited.

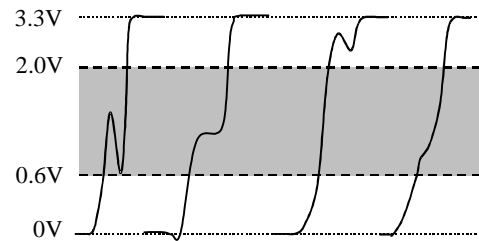
Condition	Power-supply voltage (Vddq)	Temperature(Tj)	Device
BST	3.6V	-20/-40°C(note)	High speed
TYP	3.3V	25°C	Standard
WST	3.0V	125°C	Low speed

(note) : Equal value as the lower limit value of the product in the operation guarantee temperature Ta.

(Note 2)

The example of the waveform is shown in below chart.

During the fixed time, reflected wave of becoming fixed voltage can become glitch inside SH-4.



There is a reflective wave within the range. (NG)      There is a reflective wave within the range. (NG)      There is not a reflective wave within the range.      There is a reflective wave within the range, but monotonous increase.

(Note 3)

Please refer to the following [Supplement].

(Note 4)

Please judge based on the specification of the receiving-edge side device.

In addition, after considering the substrate impedance evaluation error, please confirm the final judgement used by real machine .

(Note 5)

After considering the substrate impedance evaluation error, please confirm final judgement used by real machine.

Figure 1 : Judgment flow of IBIS simulation result

## 3. Characteristic impedance evaluation and IBIS simulation

The characteristic impedance of the board can be evaluated with a transmission route simulator (the Interconnectix made by MentorGraphics, the XTK made by Innoveda , , etc. for instance)

Moreover, it is also possible to receive the design support of the board equipped with SH-4 from Zuken Inc. as a method of raising the level of the evaluation.

Zuken Inc. is simulating the characteristic impedance extraction and IBIS of the board with a transmission route simulator.

When you evaluate the characteristic impedance without using these tools on the desk, please design with to secure enough margin.

[Supplement] Principle of glitch generation cause and measures

The outline chart when one SDRAM is connected with the CKIO part is shown in Figure 2 (Package model and substrate wiring from PIN to Rd are omitted).

The impedance of the output buffer is  $r$ , the series termination resistance is  $R_d$ , the characteristic impedance of substrate wiring is  $Z_0$ .

In A point is the pin of SH-4, in B point is pin of SDRAM.

The signal waveform output from SH-4 reflects in B point.

When the condition of " $R_d=0$  and  $r=Z_0$ ", the reflected wave is generated in the voltage of almost  $0.5 * V_{ddq}$  in A point.

The reflected wave is more or less generated as long as a complete impedance match is not achieved.

The transmission route as actually separates, and is as the branch complex as Figure 2 as the output impedance of the output buffer changes depending on the output level, too though can define potential  $V_{ar}$  and  $V_{af}$  where the reflected wave is generated.

The method of suppressing the reflected wave which adjusts each parameter as shown in Table 1, and moving the potential of the reflected wave outside the VLT(logical threshold voltage : at SH-4, it is from  $V_{IL}(\max)$  to  $V_{IH}(\min)$ .) range in the input buffer is effective as measures.

It is difficult to obtain the waveform of the reflected wave in an actual board by using an analytical expression, therefore strongly recommends confirming by the simulation.

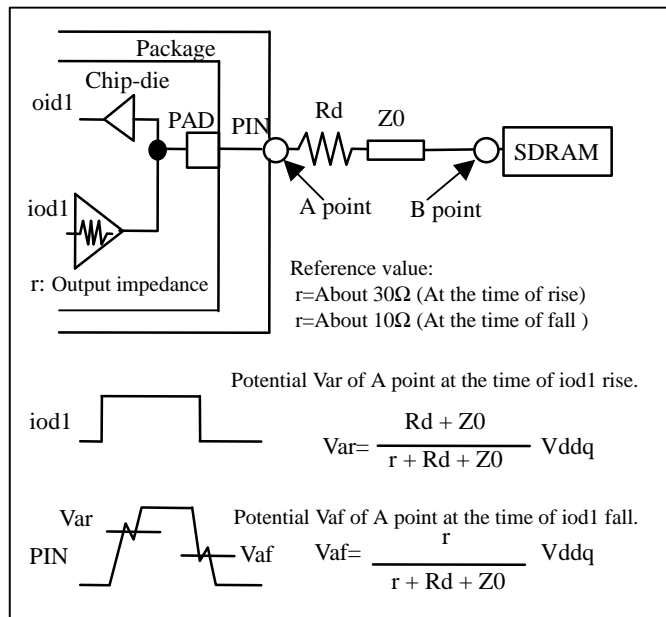


Figure 2 : Rough estimate of glitch generation potential

Table 1: Parameter and contents for adjustment

Parameter	Contents
$R_d$	The influence of the reflected wave is eased, and moves outside the VLT range in the input buffer. The signal amplitude in the receiving-end device does not swing full in the worst condition occasionally.
$Z_0$	There is a physical restriction within the range where impedance can control.
Receiving-end capacity "At Figure2 SDRAM"	The number and the capacity of the device which receives the clock are adjusted, relates to the influence of the reflected wave caused in sending-end.

